

Supporting Information

High-power Piezoelectric Behavior of Acceptor-doped <001> and <111> Textured Piezoelectric Ceramics

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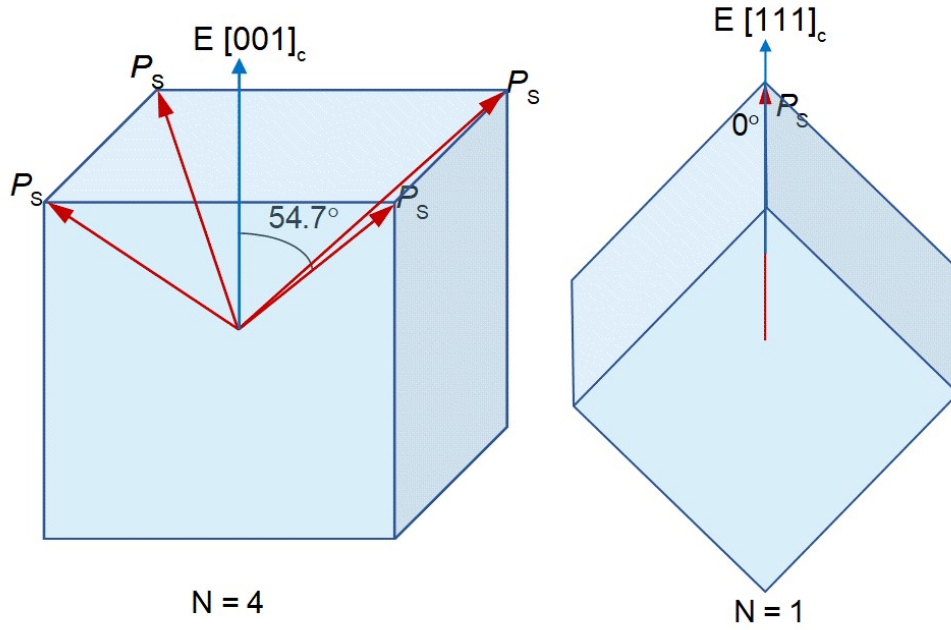


Figure S1. Engineered domain configurations for $[001]_c$ - and $[111]_c$ -oriented rhombohedral crystals.

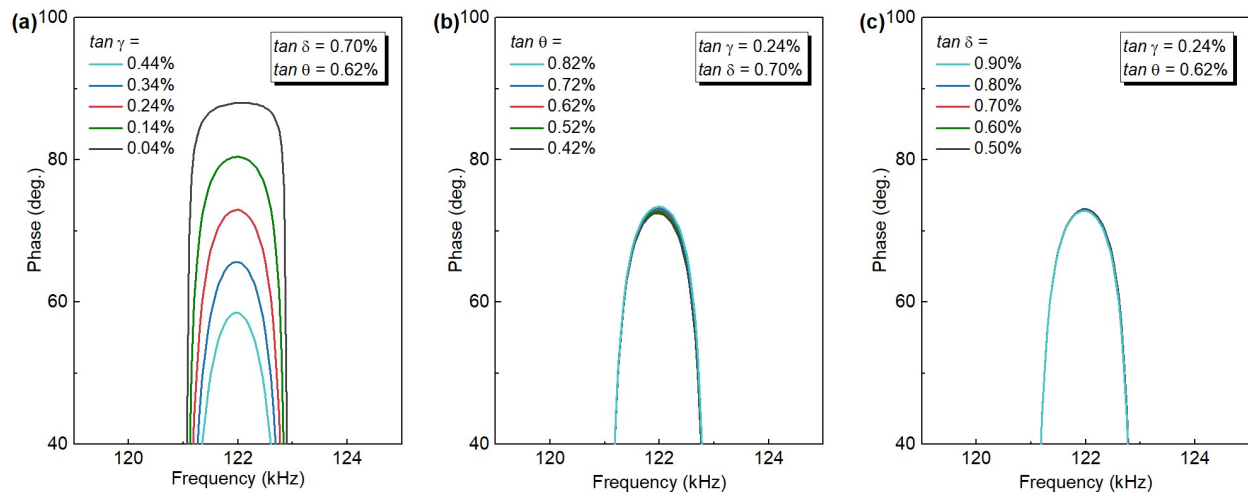


Figure S2. (a)–(c) Simulated phase angle spectra for $\langle 111 \rangle$ textured ceramic with different loss factors.

Table S1. Densities for random, <001> and <111> textured piezoelectric ceramics.

Specimen	Template	Theoretical density [g cm ⁻³]	Measured density [g cm ⁻³]	Relative density [%]
Random	0	8.19	7.92	96.7
<001> Textured	2 vol.% <001> BT	8.15	7.82	96.0
<111> Textured	2 vol.% <111> BT	8.15	7.67	94.1
Doped-<001> Textured	2 vol.% <001> BT	8.15	7.78	95.5
Doped-<111> Textured	2 vol.% <111> BT	8.15	7.69	94.4